

## SuperMOS – PDFN3\*3-8L -30V 5.8mΩ R<sub>DS(ON)</sub>, P-channel MOSFET

## 1. Description

The AONR21357-ES uses advanced trench technology MOSFETs to provide excellent  $R_{DS(ON)}$  and low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product AONR21357-ES Pb-free

#### 2. Features

- -30V  $R_{DS(ON)}$ =5.8m $\Omega$ (Typ.) @V<sub>GS</sub>=-10V  $R_{DS(ON)}$ =8m $\Omega$ (Typ.) @V<sub>GS</sub>=-4.5V
- Fast Switching
- High density cell design for low R<sub>DS(on)</sub>
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

## 3. Applications

PWM applications

Load switch

- Power management in portable/desktop PCs
- DC/DC conversion

#### 100% UIS TESTED

## 4. Ordering Information

Dort Number	Dookogo	Morking	Motorial	Doolsing	Quantity	Flammability	Reel
Part Number	Package	Marking	Material	Packing	per reel	Rating	Size
AONR21357-ES	DDEN12*2 01	ESN21357-ES/LOT	Halogen	Tape &	5,000	LII 04\/ 0	13
	PDFIN3"3-8L	E3NZ1337-E3/LU1	free	Reel	PCS	UL 94V-0	inches

# 5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
4	Gate	8 7 6 5	Q D
1/2/3	Source	ESN21357	
5/6/7/8	Drain	1 2 3 4	G



# 6. Specification

# Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limited	Unit		
Drain-Source Voltage	BV <sub>DSS</sub>	-30	V		
Gate-Source Voltage	V <sub>GS</sub>	±20	V		
Continuous Drain Current	T <sub>C</sub> =25°C		-50	^	
Continuous Drain Current	T <sub>C</sub> =100°C	- I <sub>D</sub>	-32	Α	
Maximum Payer Dissipation	T <sub>C</sub> =25°C	В	69	W	
Maximum Power Dissipation	T <sub>C</sub> =100°C	$ P_D$	28	VV	
Pulsed Drain Current	I <sub>DM</sub>	-200	Α		
Single Pulse Avalanche Current <sup>a</sup>	I <sub>AS</sub>	-40	Α		
Single Pulse Avalanche Energy <sup>a</sup>	E <sub>AS</sub>	80	mJ		
Operating Junction Temperature	TJ	150	°C		
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C		

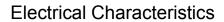
#### Thermal resistance ratings

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Case Thermal Resistance (t ≤ 10s)	R <sub>0JC</sub>		1.8	°CAM
Junction-to-Ambient Thermal Resistance	R <sub>θJA</sub>		65	°C/W

Notes:

a: The EAS data shows Max. rating The test condition is  $V_{DD}$ = -25V,  $V_{GS}$ = -10V, L= 0.1mH

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## At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions N		Тур.	Max.	Unit		
OFF CHARACTERISTICS								
Drain-to-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30			V		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =-30V			-1	uA		
Gate-to-source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA		
	ON CHA	RACTERISTICS						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.0		-2.5	٧		
Drain-to-source On-resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A		5.8	9	mΩ		
Diam-to-source On-resistance	NDS(on)	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-15A		8	14			
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-10V, I <sub>D</sub> =-20A		50		S		
CHARGES, (	CAPACITAN	NCES AND GATE RESIST	ANCE					
Input Capacitance	C <sub>ISS</sub>			3522		pF		
Output Capacitance	Coss	$V_{GS}$ =0V, $V_{DS}$ =-15V f=1MHz		465				
Reverse Transfer Capacitance	C <sub>RSS</sub>	1 1111112		370				
Total Gate Charge	Q <sub>G(TOT)</sub>			35				
Gate-to-Source Charge	Q <sub>GS</sub>	$V_{GS}$ =-10V, $V_{DS}$ =-15V $I_{D}$ =-20A		10		nC		
Gate-to-Drain Charge	$Q_{GD}$	10 2071		10.5				
SI	WITCHING	CHARACTERISTICS						
Turn-On Delay Time	t <sub>d(ON)</sub>			11				
Rise Time	t <sub>r</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V		13.3		ns		
Turn-Off Delay Time	t <sub>d(OFF)</sub>	$I_D$ =-20A, $R_G$ =3 $\Omega$		74				
Fall Time	t <sub>f</sub>			35				
BODY DIODE CHARACTERISTICS								
Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>SD</sub> =-20A	-0.45		-1.5	V		

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# 7. Typical Characteristic

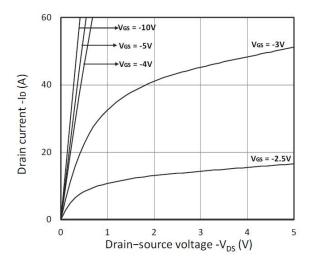


Figure 1. Output Characteristics

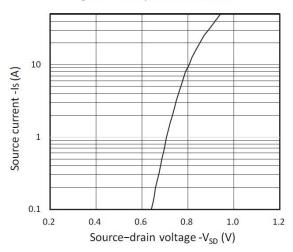


Figure 3. Forward Characteristics of Reverse

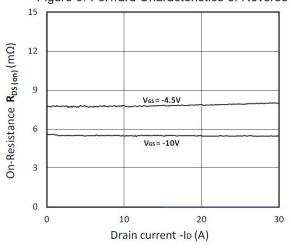


Figure 5.  $R_{DS(ON)}$  vs.  $I_D$ 

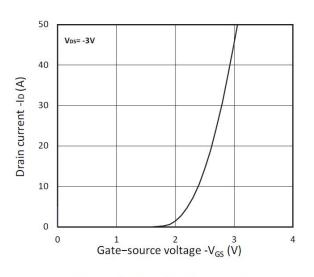
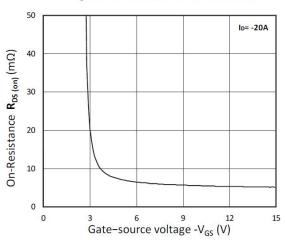


Figure 2. Transfer Characteristics



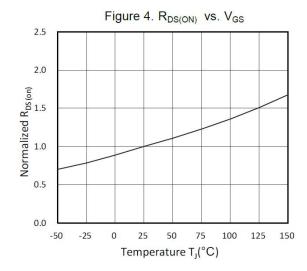
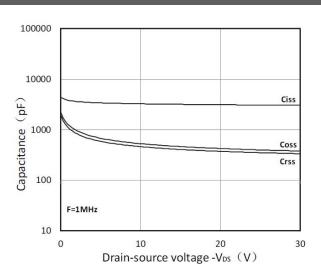


Figure 6. Normalized  $R_{\text{DS(on)}}$  vs. Temperature

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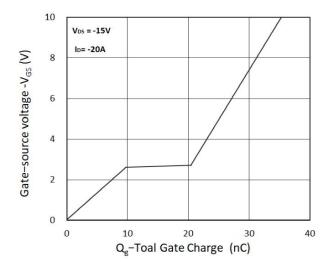


Figure 7. Capacitance Characteristics

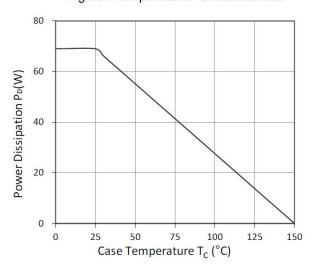
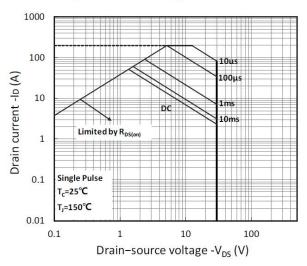


Figure 8. Gate Charge Characteristics



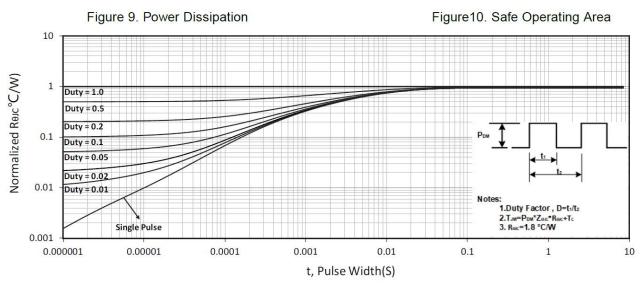
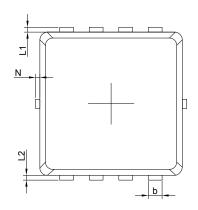
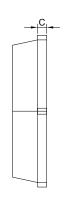


Figure 11. Normalized Maximum Transient Thermal Impedance

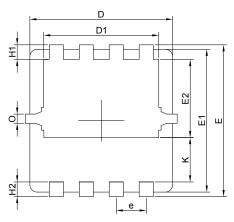


# 8. Dimension (PDFN3\*3-8L)









Symbol	Dimensions in Millimeters			Symbol	Dimensions in Millimeters			
Symbol	Symbol MIN NOM MAX Symbol	MIN	NOM	MAX				
Α	0. 65	0.75	0.85	е	0. 65 BSC.			
b	0. 25	0. 30	0. 35	H1	0. 21	0.31	0. 41	
С	0. 15	0. 20	0. 25	H2	0. 30	0. 40	0.50	
D	3. 00	3.10	3. 20	K	0.78	0. 88	0. 98	
D1	2. 40	2. 50	2. 60	L1/L2	0. 10 REF.			
Е	3. 20	3. 30	3. 40	θ	11° 12° 13		13°	
E1	3. 00	3.10	3. 20	N	0	-	0.15	
E2	1. 60	1.70	1.80	0		0. 2 REF.		

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